LN75X

GaAlAs Infrared Light Emitting Diode

For optical control systems

■ Features

- High-power output, high-efficiency: $P_O = 10 \text{ mW (typ.)}$
- High-speed modulation capability: $f_C = 12 \text{ MHz}$

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Reverse voltage	V_R	3	V
Forward current	I_{F}	100	mA
Pulse forward current *	I_{FP}	1	A
Power dissipation	P_{D}	180	mW
Operating ambient temperature	T _{opr}	-25 to +85	°C
Storage temperature	T _{stg}	-30 to +100	°C

Note) *: f = 100 Hz, Duty Cycle = 0.1%

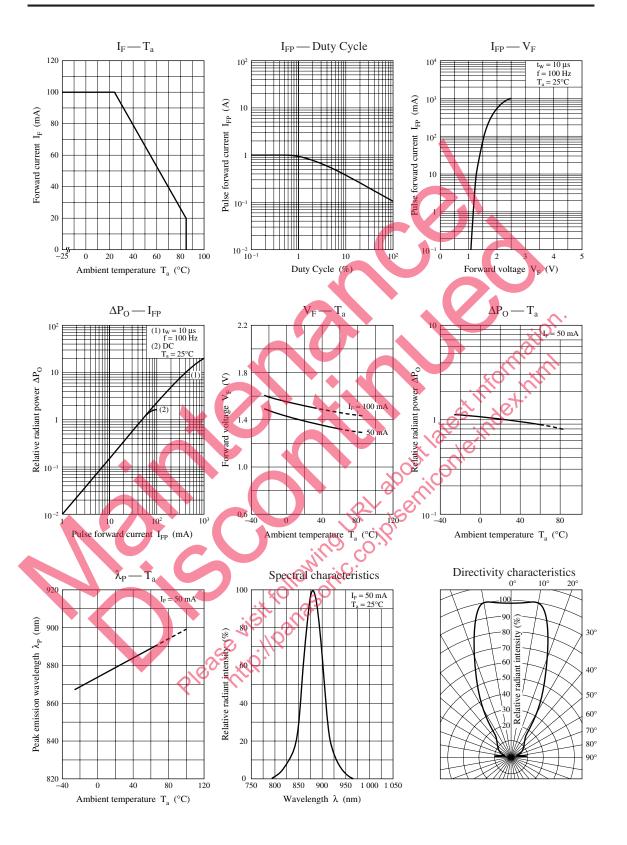
Unit: mm 4.2±0.3 (2.3) (1.9) (3.5±0.2 (4.5±0.3) (2.3) (1.9) (3.5±0.2 (4.2±0.3) (2.3) (1.9) (3.5±0.2 (4.2±0.3) (2.3) (1.9) (3.5±0.2 (4.2±0.3) (2.3) (1.9) (3.5±0.2 (4.2±0.3) (2.3) (1.9) (4.2±0.3) (2.3) (1.9) (3.5±0.15 (4.2±0.3) (4.2±0.3) (4.2±0.3) (2.3) (1.9) (3.5±0.15 (4.2±0.3) (4.2±0.3) (2.3) (1.9) (4.2±0.3) (2.54) (3.5±0.15 (4.2±0.3) (4.2

■ Electrical-Optical Characteristics T_a = 25°C ± 3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	$V_{\rm F}$	$I_{\rm F} = 100 \text{ mA}$		1.5	1.8	V
Reverse current	I_R	$V_R = 3 V$			10	μΑ
Radiant power	P_{O}	I _F = 50 mA	6	10		mW
Peak emission wavelength	λ	$I_{\rm F} = 50 \text{ mA}$		880		nm
Spectral half band width	ODAN X	$I_F = 50 \text{ mA}$		50		nm
Terminal capacitance	$C_{\rm t}$	$V_R = 0 V, f = 1 MHz$		50		pF
Half-power angle	θ	The angle when the radiant power is halved		25		٥

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. Cutoff frequency: 12 MHz
$$f_C: 10 \times log \frac{P_O \text{ at } f = f_C}{P_O \text{ at } f = 1 \text{ MHz}} = -3$$



Caution for Safety

⚠ DANGER

■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded form general industrial waste or household garbage.

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